

AUTOMOTIVE CURRENT TRANSDUCER OPEN LOOP TECHNOLOGY HAH3DR 1500-S0A





Introduction

The HAH3DR family is for the electronic measurement of DC, AC or pulsed currents in high power and low voltage automotive applications with galvanic separation between the primary circuit (high power) and the secondary circuit (electronic circuit).

The HAH3DR family gives you the choice of having different current measuring ranges in the same housing (from ± 200 A up to ± 1500 A).

Features

- · Open Loop transducer using the Hall effect
- · Low voltage application
- Unipolar +5 V DC power supply
- Primary current measuring range up to ±1500 A
- Maximum RMS primary admissible current: defined by busbar to have T < +150 °C
- Operating temperature range: -40 °C < T < +125 °C
- Output voltage: full ratio-metric (in sensitivity and offset).

Advantages

- Excellent accuracy
- Very good linearity
- Very low thermal offset drift
- Very low thermal sensitivity drift
- High frequency bandwidth
- Non insertion losses
- Very fast delay time.

Automotive applications

- Starter Generators
- Inverters
- HEV application
- EV application
- DC / DC converter.

Principle of HAH3DR family

The open loop transducers uses a Hall effect integrated circuit. The magnetic flux density B, contributing to the rise of the Hall voltage, is generated by the primary current I_p to be measured. The current to be measured I_p is supplied by a current source i.e. battery or generator (Figure 1).

Within the linear region of the hysteresis cycle, ${\it B}$ is proportional to:

$$B(I_p) = a \times I_p$$

The Hall voltage is thus expressed by:

$$U_{\text{Hall}} = (c_{\text{Hall}} / d) \times I_{\text{Hall}} \times a \times I_{\text{P}}$$

Except for $I_{\rm p}$, all terms of this equation are constant. Therefore:

$$U_{\text{Hall}} = b \times I_{\text{P}}$$

a constant

b constant

 $c_{\mbox{\tiny Hall}}$ Hall coefficient

d thickness of the Hall plate

 $I_{\mbox{\tiny Hall}}$ current across Hall plates

The measurement signal $U_{\mbox{\tiny Hall}}$ is amplified to supply the user output voltage or current.

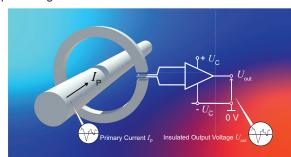


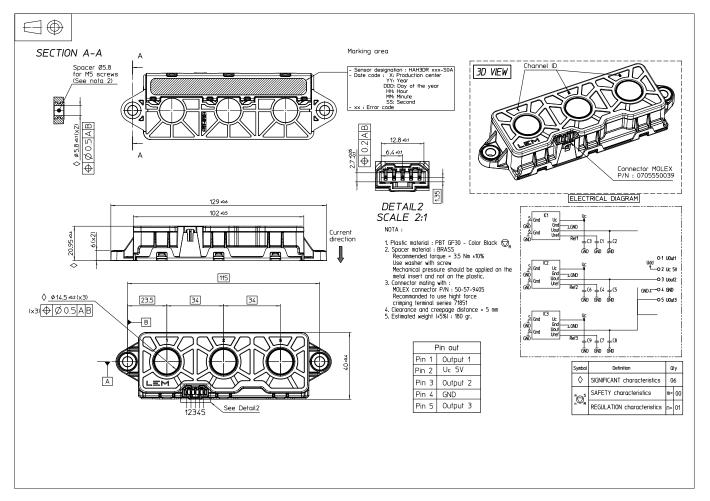
Fig. 1: Principle of the open loop transducer.

20September2023/Version 5



Dimensions (in mm)

HAH3DR 1500-S0A



Mechanical characteristics

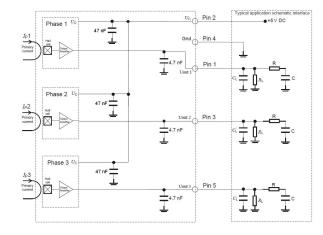
Plastic case
 PBT GF 30 % (color black)

• Mass 180 g ±5 %

Pins Copper alloy gold plated

 Degrees of protection provided by enclosure (IP Code... IPxx).

Electronic schematic



 $C_{\rm L}$ < 2.2 nF EMC protection (optional) RC Low pass filter (optional).

On board diagnostic

 $R_1 > 10 \text{ k}\Omega$. Resistor for signal line diagnostic (optional).



Absolute ratings (not operating)

HAH3DR 1500-S0A

Parameter	Symbol	Unit	Specification			Conditions
Parameter			Min	Typical	Max	Conditions
Primary withstand peak current (maximum)	\hat{I}_{Pmax}	Α			1)	
Supply voltage		V			8	Not operating
	U_{c}				6.5	Exceeding this voltage may temporarily reconfigure the circuit until next power-on
Low-level output voltage 2)	$U_{\rm outL}$	V			0.2	@ $U_{\rm C}$ = 5 V, $T_{\rm A}$ = 25 °C
High-level output voltage 2)	U_{outH}	V	4.8			@ $U_{\rm C}$ = 5 V, $T_{\rm A}$ = 25 °C
Ambient storage temperature	T_{Ast}	°C	-40		125	
Electrostatic discharge voltage (HBM)	$U_{\rm ESD\; HBM}$	kV			2	JESD22-A-114-B-class 2
RMS voltage for AC insulation test, 50 Hz, 1 min	U_{d}	kV			2.5	50 Hz, 1 min, IEC 60664 part 1
Creepage distance	d_{Cp}	mm		5		
Clearance	d_{CI}	mm		5		
Maximum reverse current 3)	I _{rev max}	mA	-80		80	
Output current	$I_{ m out}$	mA	-1		1	$R_{\rm L}$ = 10 k Ω
Insulation resistance	R_{INS}	МΩ	500			500 V DC ISO 16750

Operating characteristics in nominal range ($I_{\rm P\,N}$)

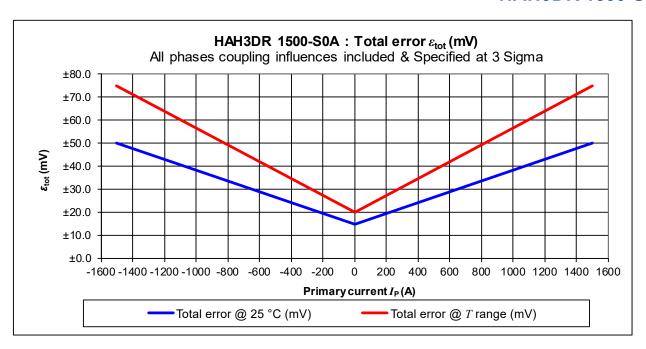
Downworker	Cumb all	11mia	Specification			Conditions	
Parameter	Symbol	Unit	Min	Typical	Max	Conditions	
Electrical Data							
Primary current, measuring range	I_{PM}	Α	-1500		1500		
Supply voltage *)	U_{c}	V	4.75	5.00	5.25		
Output voltage (Analog) 2)	U_{out}	V	$U_{\text{out}} = (U_{\text{o}})$	/5) × (U _o	$+ S \times I_{P}$	@ U _c	
Sensitivity 2)*)	S	mV/A		1.33		@ U _C = 5 V	
Offset voltage	U_{o}	V		2.5			
Current consumption (for 3 phases) *)	I_{C}	mA		45	60	@ $U_{\rm C}$ = 5 V, @ -40 < $T_{\rm A}$ < 125 °C	
Load resistance	R_{L}	ΚΩ	10				
Ambient operating temperature	T_{A}	°C	-40		125		
Load capacitance	C_{L}	nF	1	4.7	6		
Output internal resistance	$R_{\rm out}$	Ω			10	DC to 1 kHz	
	Perfo	rmance	Data 1)				
Ratiometricity error	ε_{r}	%		±0.5		@ T _A =25 °C	
Sensitivity error *)	0	%		±0.5		@ T _A = 25 °C	
Sensitivity error	$\varepsilon_{_S}$	70		±1		@ T_A = 25 °C, after T cycles	
Electrical offset voltage	$U_{\mathrm{O}\mathrm{E}}$	mV		±6		@ $T_{\rm A}$ = 25 °C, @ $U_{\rm C}$ = 5 V	
Magnetic offset voltage	$U_{\mathrm{O}\mathrm{M}}$	mV	-7.5		7.5	\bigcirc T_A = 25 °C, \bigcirc U_C = 5 V, after $\pm I_P$	
Offset voltage *)	U_{O}	mV	-15		15	@ $T_{\rm A}$ = 25 °C, @ $U_{\rm C}$ = 5 V, hysteresis included	
Average temperature coefficient of U_{OE}	$TCU_{\rm OEAV}$	mV/°C	-0.08		0.08	@ -40 °C < T < 125 °C	
Average temperature coefficient of S	TCS _{AV}	%	-0.03		0.03	@ -40 °C < T < 125 °C	
Linearity error	ε_{L}	% I _P	-1		1	@ $U_{\rm C}$ = 5 V, @ $T_{\rm A}$ = 25 °C, @ $I = I_{\rm P}$	
Delay time to 90 % to the final output value for $I_{\rm PN}$ step	t _{D 90}	μs			6	@ di/dt = 100 A/µs	
Frequency bandwidth 3)	BW	kHz	40			@ -3 dB	
Phase shift	$\Delta \varphi$	۰	-4			@ DC to 1 kHz	
Peak-to-peak noise voltage	$U_{ m nopp}$	mV			20	DC to 1 MHz	
Start-up time	$t_{ m start}$	μs			800		

Notes:

- *) The parameter with *) will be checked 100 % during the calibration phase
- $^{\rm 1)}$ Busbar temperature must be below 150 $^{\circ}{\rm C}$
- $^{2)}$ The output voltage U_{out} is fully ratiometric. The offset and sensitivity are dependent on the supply voltage U_{C} relative to the following formula:

$$I_{\rm P} = \left(\frac{5}{U_{\rm C}} \times U_{\rm out} - U_{\rm O}\right) \times \frac{1}{S} \text{ with } S \text{ in (V/A)}$$
 ³⁾ Transducer not protected against reverse polarity.

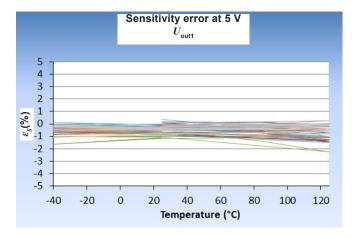


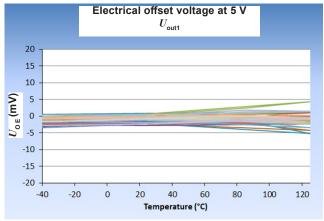


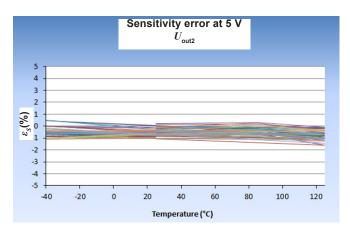
$I_{_{\mathrm{P}}}\left(A\right)$	Total error @ 25 °C (mV)	Total error @ T range (mV)
-1500	±50.0	±75.0
0	±15.0	±20.0
1500	±50.0	±75.0

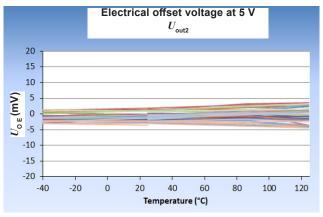


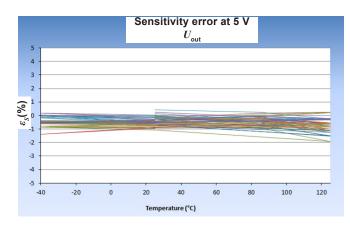
PV TEST

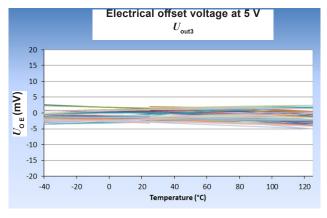






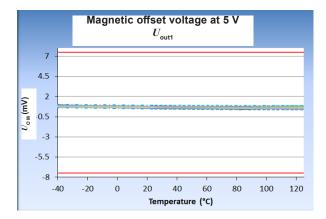


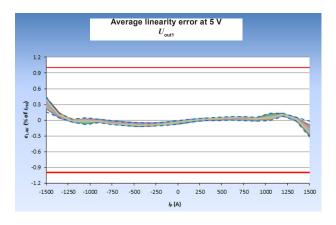


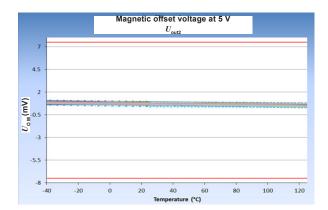


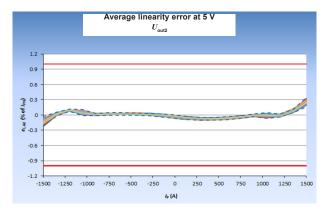


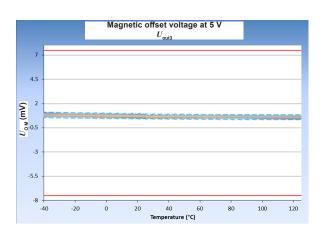
PV TEST

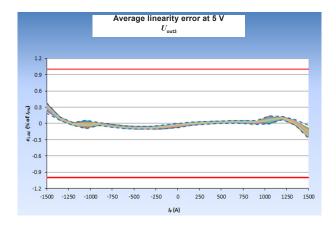






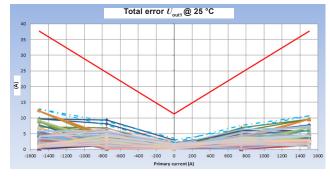


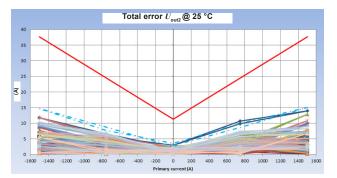


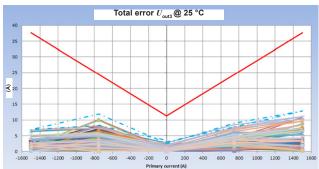


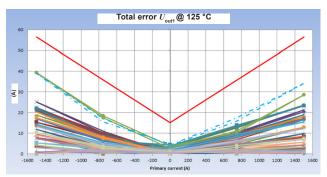


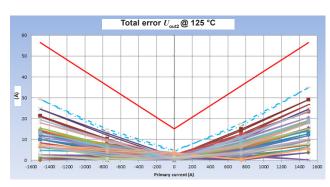
PV TEST

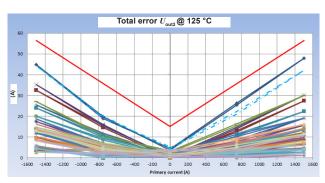


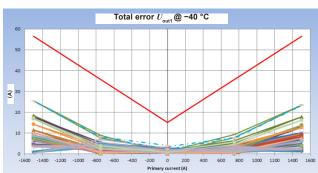


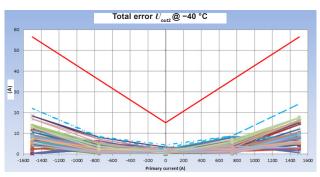


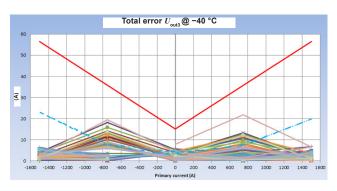








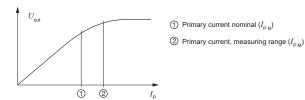






PERFORMANCES PARAMETERS DEFINITIONS

Primary current definition:



Definition of typical, minimum and maximum values:

Minimum and maximum values for specified limiting and safety conditions have to be understood as such as values shown in "typical" graphs. On the other hand, measured values are part of a statistical distribution that can be specified by an interval with upper and lower limits and a probability for measured values to lie within this interval. Unless otherwise stated (e.g. "100 % tested"), the LEM definition for such intervals designated with "min" and "max" is that the probability for values of samples to lie in this interval is 99.73 %. For a normal (Gaussian) distribution, this corresponds to an interval between -3 sigma and +3 sigma. If "typical" values are not obviously mean or average values, those values are defined to delimit intervals with a probability of 68.27 %, corresponding to an interval between -sigma and +sigma for a normal distribution. Typical, minimum and maximum values are determined during the initial characterization of a product.

Output noise voltage:

The output voltage noise is the result of the noise floor of the Hall elements and the linear amplifier.

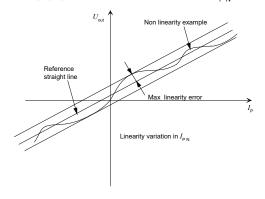
Magnetic offset:

The magnetic offset is the consequence of an any current on the primary side. It's defined after a stated excursion of primary current.

Linearity:

The maximum positive or negative discrepancy with a reference straight line $U_{\rm out}$ = $f(I_{\rm p})$.

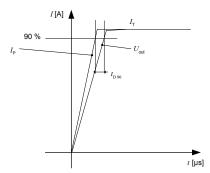
Unit: linearity (%) expressed with full scale of I_{PN} .



HAH3DR 1500-S0A

Delay time $t_{D 90}$:

The time between the primary current signal $(I_{\rm P\ N})$ and the output signal reach at 90 % of its final value.



Sensitivity:

The transducer's sensitivity S is the slope of the straight line $U_{\text{out}} = f(I_{\text{p}})$, it must establish the relation:

$$U_{\text{out}}(I_{\text{P}}) = U_{\text{C}}/5 (S \times I_{\text{P}} + U_{\text{O}})$$

Offset with temperature:

The error of the offset in the operating temperature is the variation of the offset in the temperature considered with the initial offset at 25 $^{\circ}$ C.

The offset variation $I_{O\,T}$ is a maximum variation the offset in the temperature range:

$$I_{OT} = I_{OE} \max - I_{OE} \min$$

The offset drift $TCI_{\rm O~E~AV}$ is the $I_{\rm O~T}$ value divided by the temperature range.

Sensitivity with temperature:

The error of the sensitivity in the operating temperature is the relative variation of sensitivity with the temperature considered with the initial offset at 25 $^{\circ}$ C.

The sensitivity variation S_{τ} is the maximum variation (in ppm or %) of the sensitivity in the temperature range: S_{τ} = (Sensitivity max – Sensitivity min) / Sensitivity at 25 °C.

The sensitivity drift TCS_{AV} is the S_{τ} value divided by the temperature range. Deeper and detailed info available is our LEM technical sales offices (www.lem.com).

Offset voltage @ $I_p = 0$ A:

The offset voltage is the output voltage when the primary current is zero. The ideal value of $U_{\rm O}$ is $U_{\rm C}/2$. So, the difference of $U_{\rm O}-U_{\rm C}/2$ is called the total offset voltage error. This offset error can be attributed to the electrical offset (due to the resolution of the ASIC quiescent voltage trimming), the magnetic offset, the thermal drift and the thermal hysteresis. Deeper and detailed info available is our LEM technical sales offices (www.lem. com).

Environmental test specifications:

Refer to LEM GROUP test plan laboratory CO.11.11.515.0 with "Tracking_Test Plan_Auto" sheet.

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Environmental test specifications:

HAH3DR 1500-S0A

	PV TESTS PLAN - HAH3DR	1500-S0A					
TEST	Standard or Pro	cedure	Specific conditions				
CHARACTERIZATION @ 25 °C							
Sensitivity / Total Error / Error at 0 $\pm I_{\rm PN}$	LEM CO.60.09.014.0	-					
Offset / Electrical Offset / Magnetic Offset	LEM CO.60.09.014.0	-					
Linearity error at 0 $\pm I_{PN}$	LEM CO.60.09.014.0	$\begin{array}{c} \text{Method 1: } \varepsilon_{\text{L}} \\ \text{Method 2: } \varepsilon_{\text{L}} \text{AV} \end{array}$					
Current Consumption	LEM CO.60.09.014.0	-					
С	HARACTERIZATION WITH	T°C (initial)					
Sensitivity / Total Error / Error at 0 $\pm I_{\rm PN}$	LEM CO.60.09.014.0	-					
T °C variation of / Temperature Coefficient of S	LEM CO.60.09.014.0	Method 2: TCS AV					
Offset / Electrical Offset / Magnetic Offset	LEM CO.60.09.014.0	-					
T °C variation of /Temperature Coefficient of Offset	LEM CO.60.09.014.0	Method 2: TCS _{O AV}					
	ELECTRICAL TESTS @	25 °C					
Phase delay check	LEM 98.20.00.538.0		30 Hz to 100 KHz; @ 20 A peak; ≥ −4° from DC to 1 KHz				
Frequency Bandwidth	LEM 98.20.00.538.0		30 Hz to 100 kHz; @ 20 A peak; ≥ 40 kHz @ -3 dB				
Noise measurement	LEM 98.20.00.575.0		Sweep from DC to 1 MHz ; ≤ 15 mV pp				
Delay time $\mathrm{d}i/\mathrm{d}t$	LEM 98.20.00.545.0		100 A/ μ s, I pulse = I_{PN} A; t_{D90} @ 90 % of I_{PN} \leq 6 μ s				
$\mathrm{d}u/\mathrm{d}t$	LEM 98.20.00.545.0		Slope: 5 kV/μs U = 1000 V; Criteria ≤ ±100 mV ; Disturbance < ±100 mV; Recovery time max 4 μs				
Insulation Resistance test after ageing 85/85		ISO 16750-2 § 4.12 (11/2012)	500 V DC, time = 60 s; $R_{\rm INS} \ge$ 500 MΩ Minimum. Functional test before and after test.				
Dielectric Withstand Voltage test after ageing 85/85		ISO 16750-2 § 4.12 (11/2012)	2500 V AC / 1 min / 50 Hz				
1	ENVIRONMENTAL TESTS (CLIMATIC)					
Low temperature storage test	IEC 60068-2-1 Ad (03/2007)	ISO 16750-4 § 5.1.1.1 (04/2010)	T °C = "T" °C Storage −40 °C Duration = 1000 h U _C = NO power supply (≡ unconnected) Check After stab. @ 25 °C (End test)				
High temperature storage test	IEC 60068-2-2 Bd (07/2007)	ISO 16750-4 § 5.1.2.1 (04/2010)	T °C = "T" °C Storage 125 °C Duration =1000 h U _C = NO power supply (≡ unconnected) Check After stab. @ 25 °C (End test)				
Thermal shock	IEC 60068-2-14 Na (01/2009)	ISO 16750-4 § 5.3.2 (04/2010)	T °C = " T " °C Operating −40 °C & 125 °C Duration = 1000 cycles; 30 min / 30 min $U_{\mathbb{C}}$ = NO power supply (≡ unconnected) Check After stab. @ 25 °C (End test)				
Power Temperature cycle test	IEC 60068-2-14 Nb (01/2009)	ISO 16750-4 § 5.3.1 (04/2010)	T °C = " T " °C Operating -40 °C & 125 °C 30 cycles of 8 h: ramp 1 °/min; Lower T duration 60 min, higher T duration 110 min operating from 20 ° C to 125 °C (see profile)				
Steady state <i>T</i> °C Humidity bias life test	JESD 22-A101 (03/2009)	-	T °C = 85 °C; RH = 85 %; Duration = 1000 h $U_{\rm C}$ = 5 V (\equiv connected); $I_{\rm p}$ = 0 A; Check After stab. @ 25 °C (End test)				



TEST	Standard or P	rocedure	Specific conditions			
MECHANICAL TESTS						
Sinus Vibration in T $^{\circ}$ C	IEC 60068-2-xx	ISO 16750-3 § 4.1.2.2 (12/2012)	Sinus; Level = 30 - 60 m/s²; f = 100 Hz to 440 Hz; $22 \text{ hr/axis; } -40 ^{\circ}\text{C} < T < 95 ^{\circ}\text{C}$ U_{C} = 5 V (\equiv connected); I_{p} = 0 A; Monitoring Check After stab. @ 25 $^{\circ}\text{C}$ (End test); & Meas. torque Bef. and After.			
Random Vibration in T° C	IEC 60068-2-64 (02/2008)	ISO 16750-3 § 4.1.2.2 (vib. profil: sprung masses) ISO 16750-3 § 4.1.1 (<i>T</i> °C) (12/2012)	Random; Level = 96 m/s²; $f=10~{\rm Hz} - 2000~{\rm Hz}$; 22 hour/axis; $-40~{\rm ^{\circ}C} < T < 95~{\rm ^{\circ}C}$ $U_{\rm _{C}}=5~{\rm V}~(\equiv {\rm connected}); I_{\rm _{P}}=0~{\rm A;}~{\rm Monitoring}$ Check After stab. @ 25 °C (End test); & Meas. torque Bef. and After			
Shocks	IEC 60068-2-27 (02/2008)	ISO 16750-3 § 4.2 (12/2012)	Acceleration: 500 m/s²; Duration: 6 ms; Half-sine pulse: 10 * in each direction (total 60 shocks) $U_{\rm C}$ = NO power supply Check After stab. @ 25 °C (End test); & Meas. torque Bef. and After			
Free Fall (Device not packaged)	IEC 60068-2-31 §5.2: method 1 (05/2008)	ISO 16750-3 § 4.3 (12/2012)	Height = 1 m; Concrete floor 3 axes; 2 directions by axis; 1 sample by axis			
	EMC TESTS	•				
Immunity to Electrostatic Discharges (Handling of devices)	ISO 10605 (07/2008)	-	Contact discharges: ±4.6 kV Air discharges: ±8 kV U _C = NO power supply (≡ unconnected) Criteria B			
Immunity to Conducted disturbances (BCI)	ISO 11452-4 (12/2011)	-	Level = 2 f = 1 MHz to 400 MHz Criteria A acceptance @ 5 %			
Immunity to Radiated disturbances (ALSE)	ISO 11452-2 (11/2004)	-	f = 400 MHz to 1 GHz; Level = 100 V/m (CW, AM 80 %) f = 0.8 GHz to 2 GHz; Level = 70 V/m (CW, PM PRR = 217 Hz PD = 0.57 ms) f = 1 GHz to 2 GHz; Level = 70 V/m (CW) Criteria A acceptance @ 5 %			
Immunity to Radiated disturbances (ALSE)	CISPR 25 (03/2008)	-	Table 9, Class 5 by default f = 150 kHz to 2.5 GHz			
	CONNECTOR TE	ST				
Connector test	LEM		45 N with lock; >17 N without lock, 50 cycles mate-unmate			